Functional Safety Information

DRV8143-Q1 Half Bridge Driver Functional Safety FIT Rate, FMD and Pin FMA



Anand Gopalan, Motor Drivers, TI

Table of Contents

| 1 Overview | 2 |
|---|---|
| 2 Functional Safety Failure In Time (FIT) Rates | 5 |
| 3 Failure Mode Distribution (FMD) | |
| 4 Pin Failure Mode Analysis (Pin FMA) | |
| 4.1 SPI "P" variant in HVSSOP package | |
| 4.2 SPI "S" variant in VQFN-HR package | |
| 4.3 HW variant in VQFN-HR package. | |
| 5 Revision History | |

Trademarks

All trademarks are the property of their respective owners.

Overview www.ti.com

1 Overview

This document contains information for DRV8143-Q1 to aid in a functional safety system design. This document covers all the device package and interface variants as listed below:

- SPI "P" variant in HVSSOP package
- HW variant in VQFN-HR package
- SPI "S" variant in VQFN-HR package

Information provided are:

- · Functional Safety Failure In Time (FIT) rates of the semiconductor component estimated by the application of industry reliability standards
- Component failure modes and their distribution (FMD) based on the primary function of the device
- Pin failure mode analysis (Pin FMA) for all the package and interface variants

Figure 1-1 shows the HW device variant's functional block diagram for reference.

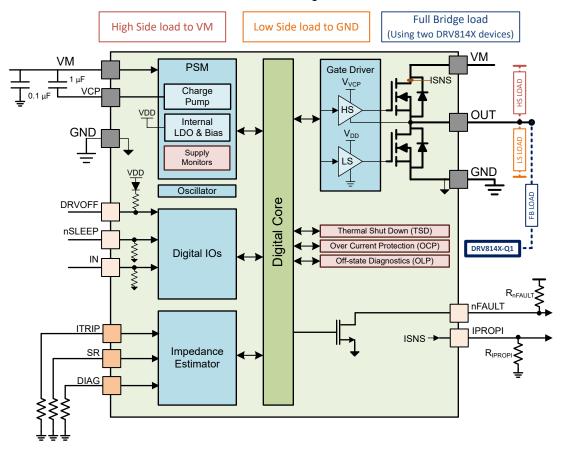


Figure 1-1. Functional Block Diagram for HW variant

Figure 1-2 shows the SPI "S" device variant's functional block diagram for reference.

www.ti.com Overview

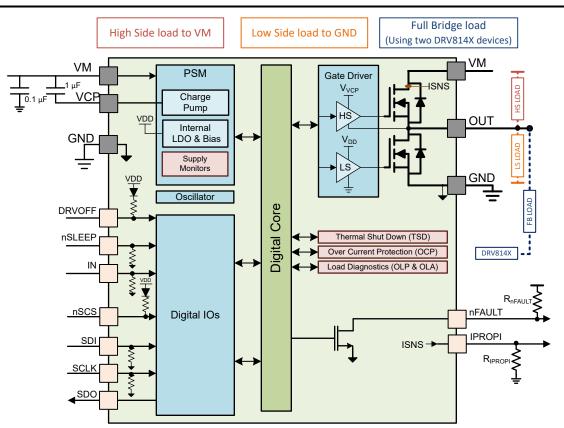


Figure 1-2. Functional Block Diagram for SPI "S" variant

Figure 1-3 shows the SPI "P" device variant's functional block diagram for reference.

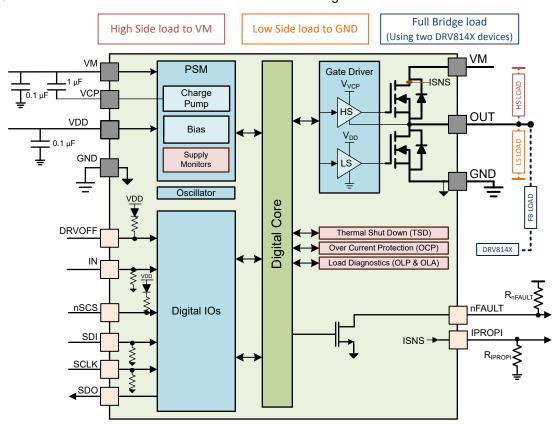


Figure 1-3. Functional Block Diagram for SPI "P" variant



Overview www.ti.com

ADVANCE INFORMATION for preproduction products; subject to change without notice.

accordance with the IEC 61508 or ISO 26262 standards.

DRV8143-Q1 was developed using a quality-managed development process, but was not developed in



2 Functional Safety Failure In Time (FIT) Rates

This section provides Functional Safety Failure In Time (FIT) rates for DRV8143-Q1 based on two different industry-wide used reliability standards:

- Table 2-1 provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- Table 2-2 provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-1. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

| | FIT (Failures Per 10 ⁹ Hours) | | | |
|------------------------------|--|-------------------------------|------------------------------------|--|
| FIT IEC TR 62380 / ISO 26262 | SPI "P" variant in HVSSOP package | HW variant in VQFN-HR package | SPI "S" variant in VQFN-HR package | |
| Total Component FIT Rate | 23 | 26 | 26 | |
| Die FIT Rate | 9 | 16 | 16 | |
| Package FIT Rate | 14 | 10 | 10 | |

The failure rate and mission profile information in Table 2-1 comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

· Mission Profile: Motor Control from Table 11

Power dissipation: 1150 mW
Climate type: World-wide Table 8
Package factor (lambda 3): Table 17b

Substrate Material: FR4EOS FIT rate assumed: 0 FIT

Table 2-2. Component Failure Rates per Siemens Norm SN 29500-2

| Table | Category | Reference FIT Rate | Reference Virtual T _J |
|-------|--|--------------------|----------------------------------|
| 5 | CMOS,BICMOS Digital, analog / mixed | 25 FIT | 55°C |

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in Table 2-2 come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.



3 Failure Mode Distribution (FMD)

The failure mode distribution estimation for DRV8143-Q1 in Table 3-1 comes from the combination of common failure modes listed in standards such as IEC 61508 and ISO 26262, the ratio of sub-circuit function size and complexity and from best engineering judgment.

The failure modes listed in this section reflect random failure events and do not include failures due to misuse or overstress.

Table 3-1. Die Failure Modes and Distribution

| Die Failure Modes | Failure Mode Distribution (%) |
|--|-------------------------------|
| Output is stuck LOW when commanded OFF (GND short) | 14% |
| Output is stuck HIGH when commanded OFF (VM short) | 14% |
| Output is stuck OFF when commanded LOW (Open) | 8% |
| Output is stuck OFF when commanded HIGH (Open) | 8% |
| Output ON resistance too high when commanded LOW | 12% |
| Output ON resistance too high when commanded HIGH | 19% |
| Low side slew rate too fast or too slow (high-side recirculation) | 5% |
| High side slew rate too fast or too slow (low-side recirculation) | 5% |
| Dead-time is too short | 1% |
| Current sense feedback incorrect | 3% |
| ITRIP current regulation incorrect | 3% |
| Incorrect communication (SPI variant)/ configuration interpretation (HW variant) | 4% ⁽¹⁾ |
| Incorrect input interpretation (nSLEEP, DRVOFF, IN) | 3% ⁽¹⁾ |
| Incorrect nFAULT assertion | 1% |

^{(1) 1%} for each pin function



4 Pin Failure Mode Analysis (Pin FMA)

This section provides a Failure Mode Analysis (FMA) of the pins for each of the device variants of DRV8143-Q1 as listed below.

- 1. SPI "P" variant in HVSSOP package
- 2. HW variant in VQFN-HR package
- 3. SPI "S" variant in VQFN-HR package

The failure modes covered in this document include the typical pin-by-pin failure scenarios:

- · Pin short-circuited to Ground
- · Pin open-circuited
- · Pin short-circuited to an adjacent pin
- Pin short-circuited to supply

The analysis also indicates how these pin conditions can affect the device as per the failure effects classification in Table 4-1.

Table 4-1. TI Classification of Failure Effects

| Class | Failure Effects |
|-------|---|
| Α | Potential device damage that affects functionality |
| В | No device damage, but loss of functionality |
| С | No device damage, but performance degradation |
| D | No device damage, no impact to functionality or performance |



Following are the assumptions of use and the device configuration assumed for the pin FMA in this section:

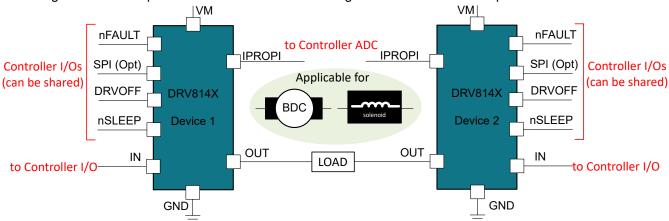


Figure 4-1. Using dual DRV814x-Q1 as a Full Bridge configuration with low-side recirculation

- · Test conditions:
 - $-~V_{VM}$ = 13.5 V, $T_{Ambient}$ = 25°C , SPI "P" variant: V_{VDD} = 5 V
- SPI "S" and "P" variant:
 - DRVOFF (pins combined) and IN pins controlled by controller
 - IPROPI (pins combined) monitored by controller, nFAULT (pins combined) monitoring optional
 - Configurations: SPI IN unlocked with
 - DRVOFF SEL = 1'b0 (Pin and register control for redundant shutoff)
 - IN_SEL for switching half bridge device = 1'b1 (Pin only control for PWM)
 - IN SEL for non-switching half bridge device = 1'b0 (Register only control)
- HW variant:
- nSLEEP, DRVOFF, EN/IN1, PH/IN2 pins controlled by controller
 - nFAULT and IPROPI pins monitored by controller
 - NC pin floating



4.1 SPI "P" variant in HVSSOP package

Figure 4-2 shows the pin diagram. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the DRV8143-Q1 data sheet.

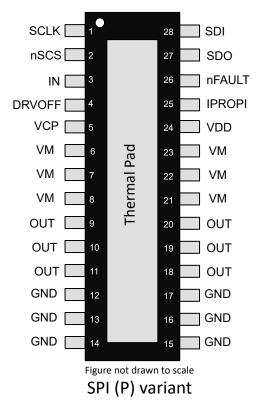


Figure 4-2. SPI "P" variants

Table 4-2. Pin FMA for Device Pins Short-Circuited to Ground

| Pin | | | |
|------------------------|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | SCLK | SPI communication is lost. | В |
| 2 | nSCS | SPI communication is lost. | В |
| 3 | IN | External PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| 4 | DRVOFF | Pin based shutoff function is lost. | В |
| 5 | VCP | Device damage possible. Device behavior can not be guaranteed. | Α |
| 6, 7, 8, 21, 22, 23 | VM | Device is powered off with driver Hi-Z. | В |
| 9, 10, 11, 18, 19, 20 | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| 12, 13, 14, 15, 16, 17 | GND | Normal function. | D |
| 24 | nSLEEP | Both "S" & "P" variants: Device will be in SLEEP state and OUT is Hi-Z | В |
| 24 | VDD | BOULT S & P VALIABLES. Device will be it SLEEP state and OOT is ni-2 | ь |
| 25 | IPROPI | IPROPI feedback is lost. ITRIP regulation, if enabled, is also lost. | В |
| 26 | nFAULT | False fault signaling possible. Device will continue to operate as commanded. | В |
| 27 | SDO | SPI communication is lost. | В |
| 28 | SDI | SPI communication is lost. | В |



Table 4-3. Pin FMA for Device Pins Open-Circuited

| Pi | n | | Failure |
|------------------------|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | SCLK | SPI communication is lost. | В |
| 2 | nSCS | SPI communication is lost. | В |
| 3 | IN | External PWM control is lost. Internal ITRIP regulation is OK. No risk of spin direction reversal. | В |
| 4 | DRVOFF | Pin based shutoff is triggered and OUT is Hi-Z | В |
| 5 | VCP | The driver can't keep up with PWM frequency > 20 KHz | В |
| 6, 7, 8, 21, 22, 23 | VM | Device is powered off with driver Hi-Z. | В |
| 9, 10, 11, 18, 19, 20 | OUT | Load drive capability is lost. | В |
| 12, 13, 14, 15, 16, 17 | GND | Normal function. | D |
| 24 | nSLEEP | Both "S" & "P" variants: Device will be in SLEEP state and OUT is Hi-Z. | В |
| 24 | VDD | BOULT S & P VALIABLES. Device will be IT SLEEP state and OUT IS RI-Z. | Ь |
| 25 | IPROPI | IPROPI feedback is lost. Load will be forced to recirculate if ITRIP regulation is enabled. | В |
| 26 | nFAULT | False fault signaling possible. Device will continue to operate as commanded. | В |
| 27 | SDO | SPI communication is lost. | В |
| 28 | SDI | SPI communication is lost. | В |

Table 4-4. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

| | 14510 4 4.1 1111 | MA for Device Pins Short-Circuited to Adjacent Pin | |
|----------|------------------|---|----------------------------|
| Short be | tween pins | Description of Potential Failure Effect(s) | Failure Effect Class |
| SCLK | SDI | SPI communication is lost. | В |
| nSCS | SCLK | SPI communication is lost. | В |
| IN | nSCS | SPI communication is affected. External PWM control is lost. Internal ITRIP regulation is OK. No risk of spin direction reversal. | В |
| DRVOFF | IN | Either OUT is Hi-Z or external PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| VCP | DRVOFF | Device damage possible. Device behavior can not be guaranteed. | Α |
| VM | VCP | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| OUT | VM | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| GND | OUT | If OUT1 is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| nSLEEP | | "S" variant: SLEEP functionality is lost. | В |
| VDD | VM | "P" variant: Device damage possible. Device behavior can not be guaranteed. | Α |
| IPROPI | nSLEEP | "S" variant: IPROPI feedback is inaccurate. ITRIP regulation levels, if enabled, will be lower. | В |
| IFIXOFI | VDD " | "P" variant: IPROPI feedback is inaccurate. OUT is Hi-Z if ITRIP regulation is enabled. | |
| nFAULT | IPROPI | False fault signaling possible. IPROPI feedback is inaccurate. ITRIP regulation levels, if enabled, will be lower. | В |
| SDO | nFAULT | False fault signaling possible. SPI communication will be affected during fault assertion. | В |
| SDI | SDO | SPI communication is lost. | В |

Table 4-5. Pin FMA for Device Pins Short-Circuited to supply VM

| F | Pin | Description of Detection Follows Effection | Failure |
|-----|------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | SCLK | Device damage possible. | Α |
| 2 | nSCS | Device damage possible. | Α |



Table 4-5. Pin FMA for Device Pins Short-Circuited to supply VM (continued)

| Pin | | | |
|------------------------|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 3 | IN | Device damage possible. | Α |
| 4 | DRVOFF | OUT is Hi-Z. | В |
| 5 | VCP | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| 6, 7, 8, 21, 22, 23 | VM | Normal function. | D |
| 9, 10, 11, 18, 19, 20 | OUT | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| 12, 13, 14, 15, 16, 17 | GND | Device is powered off with driver Hi-Z. | В |
| 24 | nSLEEP | Device damage possible. | Α |
| 24 | VDD | Device damage possible. | Α |
| 25 | IPROPI | Device damage possible. | Α |
| 26 | nFAULT | Device damage possible. | Α |
| 27 | SDO | Device damage possible. | Α |
| 28 | SDI | Device damage possible. | Α |



4.2 SPI "S" variant in VQFN-HR package

Figure 4-3shows the pin diagram. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the DRV8143-Q1 data sheet.

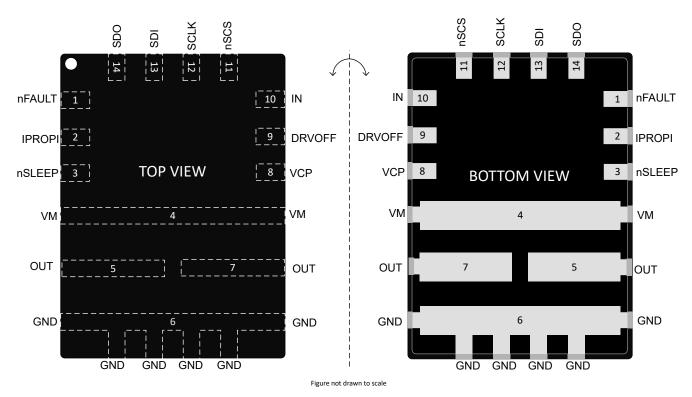


Figure 4-3. SPI "S" variant

Table 4-6. Pin FMA for Device Pins Short-Circuited to Ground

| Pin | | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | nFAULT | False fault signaling possible. Device will continue to operate as commanded. | В |
| 2 | IPROPI | IPROPI feedback is lost. ITRIP regulation, if enabled, is also lost. | В |
| 3 | nSLEEP | Device will be in SLEEP state and OUT is Hi-Z | В |
| 4 | VM | Device is powered off with driver Hi-Z. | В |
| 5 | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| 6 | GND | Normal function. | D |
| 7 | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| 8 | VCP | Device damage possible. Device behavior can not be guaranteed. | Α |
| 9 | DRVOFF | Pin based shutoff function is lost. | В |
| 10 | IN | External PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| 11 | nSCS | SPI communication is lost. | В |
| 12 | SCLK | SPI communication is lost. | В |
| 13 | SDI | SPI communication is lost. | В |
| 14 | SDO | SPI communication is lost. | В |



Table 4-7. Pin FMA for Device Pins Open-Circuited

| Pin | | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | nFAULT | False fault signaling possible. Device will continue to operate as commanded. | В |
| 2 | IPROPI | IPROPI feedback is lost. Load will be forced to recirculate if ITRIP regulation is enabled. | В |
| 3 | nSLEEP | Device will be in SLEEP state and OUT is Hi-Z. | В |
| 4 | VM | Device is powered off with driver Hi-Z. | В |
| 5 | OUT | Load drive capability is lost. | В |
| 6 | GND | Normal function. | D |
| 7 | OUT | Load drive capability is lost. | В |
| 8 | VCP | The driver can't keep up with PWM frequency > 20 KHz | В |
| 9 | DRVOFF | Pin based shutoff is triggered and OUT is Hi-Z | В |
| 10 | IN | External PWM control is lost. Internal ITRIP regulation is OK. No risk of spin direction reversal. | В |
| 11 | nSCS | SPI communication is lost. | В |
| 12 | SCLK | SPI communication is lost. | В |
| 13 | SDI | SPI communication is lost. | В |
| 14 | SDO | SPI communication is lost. | В |

Table 4-8. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

| | 14510 + 0.1 1111 | TWA for Device Fills Short-Circuited to Adjacent Fill | |
|--------------------|------------------|---|----------------------------|
| Short between pins | | Description of Potential Failure Effect(s) | Failure Effect Class |
| nFAULT | SDO | False fault signaling possible. SPI communication will be affected during fault assertion. | В |
| IPROPI | nFAULT | False fault signaling possible. IPROPI feedback is inaccurate. ITRIP regulation levels, if enabled, will be lower. | В |
| nSLEEP | IPROPI | ITRIP regulation levels, if enabled, will be lower. | В |
| VM | nSLEEP | SLEEP functionality is lost. | В |
| OUT | VM | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| GND | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| VCP | VM | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| DRVOFF | VCP | Device damage possible. Device behavior can not be guaranteed. | Α |
| IN | DRVOFF | Either OUT is Hi-Z or external PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| nSCS | IN | SPI communication is affected. External PWM control is lost. Internal ITRIP regulation is OK. No risk of spin direction reversal. | В |
| SCLK | nSCS | SPI communication is lost. | В |
| SDI | SCLK | SPI communication is lost. | В |
| SDO | SDI | SPI communication is lost. | В |



Table 4-9. Pin FMA for Device Pins Short-Circuited to VM

| Table 4 of 1 min to before 1 me entered to 1 min | | | |
|--|----------|--|----------------------------|
| No. | Pin Name | Description of Potential Failure Effect(s) | Failure Effect Class |
| 1 | nFAULT | Device damage possible. | А |
| 2 | IPROPI | Device damage possible. | А |
| 3 | nSLEEP | SLEEP functionality is lost. | В |
| 4 | VM | Device is powered off with driver Hi-Z. | В |
| 5 | OUT | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| 6 | GND | Normal function. | D |
| 7 | OUT | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| 8 | VCP | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| 9 | DRVOFF | OUT is Hi-Z. | В |
| 10 | IN | Device damage possible. | Α |
| 11 | nSCS | Device damage possible. | А |
| 12 | SCLK | Device damage possible. | А |
| 13 | SDI | Device damage possible. | А |
| 14 | SDO | Device damage possible. | Α |



4.3 HW variant in VQFN-HR package

Figure 4-4shows the pin diagram. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the DRV8143-Q1 data sheet.

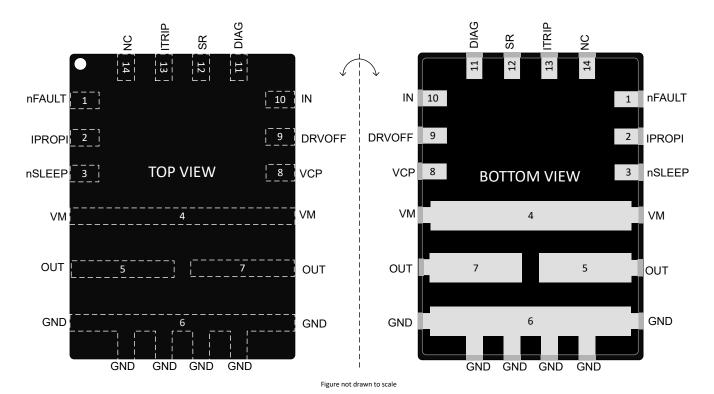


Figure 4-4. HW variant

Table 4-10. Pin FMA for Device Pins Short-Circuited to Ground

| P | in | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | nFAULT | False fault signalling. Devie will continue to operate as commanded. | В |
| 2 | IPROPI | IPROPI feedback is lost. ITRIP regulation, if enabled, is also lost. | В |
| 3 | nSLEEP | Device will be in SLEEP state and outputs are Hi-Z | В |
| 4 | VM | Device is powered off with driver Hi-Z. | В |
| 5 | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| 6 | GND | Normal function. | D |
| 7 | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| 8 | VCP | Device damage possible. Device behavior can not be guaranteed. | Α |
| 9 | DRVOFF | Shutoff function is lost. | В |
| 10 | IN | External PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| 11 | DIAG | Wrong load and fault response configuration possible. | В |
| 12 | SR | Wrong SR configuration possible, EM performance may be affected. | В |
| 13 | ITRIP | Incorrect ITRIP level for current regulation possible. | В |
| 14 | NC | Unused pin. | D |



Table 4-11. Pin FMA for Device Pins Open-Circuited

| Pin | | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | nFAULT | False fault signalling. Devie will continue to operate as commanded. | В |
| 2 | IPROPI | IPROPI feedback is lost. Load will be forced to recirculte if ITRIP regulation is enabled. | В |
| 3 | nSLEEP | Device will be in SLEEP state and outputs are Hi-Z | В |
| 4 | VM | Device is powered off with driver Hi-Z. | В |
| 5 | OUT | Load drive capability is lost. | В |
| 6 | GND | Normal function. | D |
| 7 | OUT | Load drive capability is lost. | В |
| 8 | VCP | The driver can't keep up with PWM frequency > 20 KHz. | В |
| 9 | DRVOFF | Pin based shutoff is triggered and OUT is Hi-Z. | В |
| 10 | IN | External PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| 11 | DIAG | Wrong load and fault response configuration possible. | В |
| 12 | SR | Wrong SR configuration possible, EM performance may be affected. | В |
| 13 | ITRIP | Incorrect ITRIP level for current regulation possible. | В |
| 14 | NC | Not used. | D |

Table 4-12. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

| Short between pins | | Description of Potential Failure Effect(s) | Failure Effect Class |
|--------------------|--------|--|----------------------------|
| nFAULT | NC | Fault signaling function is unaffected. | D |
| IPROPI | nFAULT | False fault signaling possible. IPROPI feedback is inaccurate. ITRIP regulation levels, if enabled, will be lower. | В |
| nSLEEP | IPROPI | IPROPI feedback is inaccurate. ITRIP regulation levels, if enabled, will be lower. | В |
| VM | nSLEEP | SLEEP functionality is lost. | В |
| OUT | VM | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| GND | OUT | If OUT is commanded to be pulled high, short is detected and OUT is Hi-Z. | В |
| VCP | VM | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| DRVOFF | VCP | Device damage possible. Device behavior can not be guaranteed. | Α |
| IN | DRVOFF | Either OUT is Hi-Z or external PWM control is lost. Internal ITRIP regulation is ok. No risk of spin direction reversal. | В |
| DIAG | IN | Wrong load and fault response configuration possible. Internal ITRIP regulation is OK. No risk of spin direction reversal. | В |
| SR | DIAG | Wrong configuration - EM performance may be affected. Load and fault response may be incorrect. | В |
| ITRIP | SR | Wrong configuration - EM performance may be affected. Incorrect ITRIP level for current regulation possible. | В |
| NC | ITRIP | ITRIP setting is unaffected. | D |

Table 4-13. Pin FMA for Device Pins Short-Circuited to VM

| Pin | | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 1 | nFAULT | Device damage possible. | Α |
| 2 | IPROPI | Device damage possible. | Α |
| 3 | nSLEEP | SLEEP functionality is lost. | В |
| 4 | VM | Normal function. | D |
| 5 | OUT | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| 6 | GND | Normal function. | D |

www.ti.com Revision History

Table 4-13. Pin FMA for Device Pins Short-Circuited to VM (continued)

| Pin | | | Failure |
|-----|--------|--|-----------------|
| No. | Name | Description of Potential Failure Effect(s) | Effect Class |
| 7 | OUT | If OUT is commanded to be pulled low, short is detected and OUT is Hi-Z. | В |
| 8 | VCP | Pull up path R _{ON} (High-side FET) will be much higher. | В |
| 9 | DRVOFF | OUT is Hi-Z. | В |
| 10 | IN | Device damage possible. | Α |
| 11 | DIAG | Device damage possible. | Α |
| 12 | SR | Device damage possible. | Α |
| 13 | ITRIP | Device damage possible. | Α |
| 14 | NC | Device damage possible. | Α |

5 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated